Contents

Preface ix

5TH INTERNATIONAL CONFERENCE ON METALORGANIC VAPOR PHASE EPITAXY

SECTION I. GROWTH MECHANISM AND REACTION KINETICS

Detailed models of the MOVPE process *
K.F. Jensen, D.I. Fotiadis and T.J. Mountziaris 1
Gas phase studies of MOVPE by optical methods *
W. Richter, P. Kurpas, R. Lückerath, M. Motzkus and R. Waschbüsch 13
Thermal decomposition studies of group V hydrides
P. Abraham, A. Bekkaoui, V. Soulière, J. Bouix and Y. Monteil 26
Comparative pyrolysis studies of ethylarsines
S.H. Li, C.A. Larsen and G.B. Stringfellow 32
Surface science studies of MOVPE processes: a review of progress *
M.E. Pemble, D.S. Buhaenko, S.M. Francis, P.A. Goulding and J.T. Allen 37
In situ monitoring of crystal growth by reflectance difference spectroscopy *
E. Colas, D.E. Aspnes, R. Bhat, S.S. Studna, J.P. Harbison, L.T. Florez, M.A. Koza and V.G. Keramidas 47
Surface processes during growth of GaAs by MOCVD
L.J. Giling and M.H.J.M. de Croon 56
In-situ monitoring of GaAs growth process in MOVPE by surface photo-absorption method
N. Kobayashi, T. Makimoto, Y. Yamauchi and Y. Horikoshi 62
Reflectance-difference study of surface chemistry in MOVPE growth
L. Samuelson, K. Deppert, S. Jeppesen, J. Jönsson, G. Paulsson and P. Schmidt 68

SECTION II. ATOMIC LAYER AND PULSED FLOW EPITAXY

Atmospheric pressure atomic layer epitaxy: mechanisms and applications *
P.D. Dapkus, B.Y. Maa, Q. Chen, W.G. Jeong and S.P. DenBaars 73
Atomic layer epitaxy of $Al_xGa_{1-x}As$ and device quality GaAs
J.R. Gong, P.C. Colter, D. Jung, S.A. Hussien, C.A. Parker, A. Dip, F. Hyuga, W.M. Duncan and S.M. Bedair 83
High carbon doping of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) by atomic layer epitaxy for device applications
B.-C. Chung, R.T. Green and H.F. MacMillan 89
Ordered GaInP by atomic layer epitaxy
B.T. McDermott, N.A. El-Masry, B.L. Jiang, F. Hyuga, S.M. Bedair and W.M. Duncan 96
Pulsed jet epitaxy of III–V compounds *
M. Ozeki, N. Ohtsuka, Y. Sakuma and K. Kodama 102
GaAs epitaxy using alternate pulses in a standard LP-MOVPE reactor
J. Wisser, P. Czuprin, D. Grundmann, P. Balk, M. Waschbüsch, R. Lückerath and W. Richter 111

* Invited paper.

SECTION III. SELECTIVE AREA GROWTH

Selective epitaxy of GaAs, $Al_xGa_{1-x}As$, and $In_xGa_{1-x}As$ *
T.F. Kuech, M.S. Goorsky, M.A. Tischler, A. Palevski, P. Solomon, R. Potemski, C.S. Tsai, J.A. Lebens and K.J. Vahala 116
Selective area epitaxy of GaAs on Si using atomic layer epitaxy by LP-MOVPE
N.H. Karam, V. Haven, S.M. Vernon, N. El-Masry, E.H. Lingunis and N. Haegel 129
Patterned crystal growth of GaAs using laser scanning with atomic layer epitaxy
S. Iwai, T. Meguro, Y. Aoyagi and T. Miyoshi 136
Selective embedded growth of GaInAs by low pressure MOVPE
O. Kayser, B. Opitz, B. Westphalen, U. Niggebrügge, K. Schneider and P. Balk 141
Selective area MOVPE of GaInAs/InP heterostructures on masked and nonplanar (100) and {111} substrates
Y.D. Galeuchet and P. Roentgen 147
Composition of selectively grown $In_xGa_{1-x}As$ structures from locally resolved Raman spectroscopy
J. Finders, J. Geurts, A. Kohl, M. Weyers, B. Opitz, O. Kayser and P. Balk 151
Selective MOVPE of semi-insulating InP layers for high speed OEICs
G. Laube, A. Nowitzki, K. Dütting and P. Speier 156
Non-planar MOVPE growth using a novel shadow-masking technique
P. Demeester, L. Buydens, I. Moerman, D. Lootens and P. Van Daele 161

SECTION IV. GROWTH RELATED STUDIES

IV.A. *The role of reactors*

Layer uniformity in a multiwafer MOVPE reactor for III–V compounds *
P.M. Frijlink, J.L. Nicolas and P. Suchet 166
Influence of gas mixing on the lateral uniformity in horizontal MOVPE reactors
I. Moerman, G. Coudenys, P. Demeester, B. Turner and J. Crawley 175
Influence of gas mixing and expansion in horizontal MOVPE reactors
N.J. Mason and P.J. Walker 181
Growth of extremely uniform III–V compound semiconductor layers by LP-MOVPE by application of the gas foil technique for substrate rotation
D. Schmitz, G. Strauch, H. Jürgensen and M. Heyen 188
Uniformity – optical properties of GaInP–GaAlInP layers grown by MOVPE
M. Mpaskoutas, C. Morhaïm, J.N. Patillon, J.P. André, A. Valster and J.J. Rusch 192
MOVPE growth of II–VI compounds in a vertical reactor with high-speed horizontal rotating disk
G.S. Tompa, T. Salagaj, L. Cook, R.A. Stall, C.R. Nelson, P.L. Anderson, W.H. Wright, W.L. Ahlgren and S.M. Johnson 198

IV.B. *Growth and characterization*

Etching of InP by HCl in an OMVPE reactor
C. Caneau, R. Bhat, M. Koza, J.R. Hayes and R. Esagui 203
Plasma MOVPE of ternary and quaternary layers
M. Behet, A. Brauers and P. Balk 209
The influence of growth conditions on the planarity of MOVPE grown GaInAs(P) interfaces
P.C. Spurdens, M.R. Taylor, M. Hockly and M.J. Yates 215
Effect of wafer cleavage on composition of InGaAsP grown on InP by low pressure MOCVD
D.G. Knight, C.J. Miner and B. Watt 221
Lateral and longitudinal patterning of semiconductor structures by crystal growth on nonplanar and dielectric-masked GaAs substrates: application to thickness-modulated waveguide structures
E. Colas, A. Shahar, B.D. Soole, W.J. Tomlinson, J.R. Hayes, C. Caneau and R. Bhat 226
Step-flow growth and fractional-layer superlattices on $(\bar{1}\bar{1}\bar{1})$B GaAs vicinal surfaces
T. Fukui and H. Saito 231
Strong enhancement of band edge PL intensity and improved morphology for AlGaAs grown on lenticular GaAs substrates by low pressure MOVPE
E.S. Johnson 237

Direct evidence of lateral bandgap patterning on stepped structures grown on non-planar, vicinal GaAs surfaces by cathodoluminescence investigations
E. Colas, E.M. Clausen, Jr., E. Kapon, D.M. Hwang, S. Simhony, R. Bhat, C.Y. Chen, P.S.D. Lin, L. Schiavone and B. Van der Gaag 243
Infrared spectroscopic determination of substitutional carbon in MOVPE grown films of GaAs
A.V. Annapragada, K.F. Jensen and T.F. Kuech 248

IV.C. *Doping*

Doping level anomalies resulting from exposure to dopant precursors during cooling in MOVPE
S. Cole, L. Davis, W.J. Duncan, E.M. Marsh, R.H. Moss, W.J.M. Rothwell, P.J. Skevington and G.D.T. Spiller 254
Silicon spike-doping of GaAs with AP-MOVPE
P. Schmidt, K. Deppert and H. Kostial 259
The influence of substrate orientation and mis-orientation on the Si-doping of GaAs grown by MOVPE
X. Tang, J. te Nijenhuis, Y. Li and L.J. Giling 263
Acceptor doping of (Al,Ga)As using carbon by metalorganic vapor phase epitaxy
M.A. Tischler, R.M. Potemski, T.F. Kuech, F. Cardone, M.S. Goorsky and G. Scilla 268
On the "tunnel" diffusion of iron dopant in InP
E.W.A. Young and G.M. Fontijn 274
Carbon doping exceeding 10^{20} cm^{-3} in GaAs grown by AP-MOVPE **
M.C. Hanna, Z.H. Lu, E.W. Mao, T. McCormick, E.G. Oh, A. Majerfeld and D.M. Szmyd 279

SECTION V. NEW PRECURSORS FOR III–V AND II–VI COMPOUNDS

V.A. *Synthesis and properties*

Alternative precursors for III–V MOVPE criteria for evaluation *
A. Brauers 281
Alternative Group V precursors for CVD applications *
R.M. Lum and J.K. Klingert 290
Precursors for II–VI semiconductors: requirements and developments *
A.C. Jones, P.J. Wright and B. Cockayne 297
Physical properties of non-pyrophoric group III precursors for MOVPE
L. Pohl, M. Hostalek, H. Schumann, U. Hartmann, W. Wassermann, A. Brauers, G.K. Regel, R. Hövel, P. Balk and F. Scholz 309
Detection of phenylarsine in air
J. Zacheja, A. Schütze, A. Brauers and D. Kohl 314
Screening of organotellurium compounds for use as MOVPE precursors
J.E. Hails and S.J.C. Irvine 319
Synthesis and decomposition studies of dialkyltellurides of type RTeR′
A.E.D. McQueen, P.N. Culshaw, J.C. Walton, D.V. Shenai-Khatkhate, D.J. Cole-Hamilton and J.B. Mullin 325

V.B. *Growth with new precursors*

Epitaxial growth of GaAs with $(C_2H_5)_2GaCl$ and AsH_3 in a hot-wall system
N.I. Buchan, T.F. Kuech, M.A. Tischler and R. Potemski 331
Growth of GaAs by MOCVD using a solid arsenic source
R. Peña-Sierra, J.G. Castro-Zavala and A. Escobosa 337
Control of residual impurity incorporation in tertiarybutylarsine-grown GaAs
G. Haacke, S.P. Watkins and H. Burkhard 342
Trisdimethylaminoarsine as As source for the LP-MOVPE of GaAs **
M.H. Zimmer, R. Hövel, W. Brysch, A. Brauers and P. Balk 348

** Extended abstract.

Growth of low carbon content $Al_xGa_{1-x}As$ by reduced pressure MOVPE using trimethylamine alane **
A.C. Jones and S.A. Rushworth 350
Growth of GaInP over the whole composition range by OMVPE using tertiarybutylphosphine for the phosphorus source
Y. Takeda, S. Araki, M. Takemi, S. Noda and A. Sasaki 351
Growth of InP with novel In and P precursors
R. Hövel, N. Brianese, A. Brauers, P. Balk, M. Zimmer, M. Hostalek and L. Pohl 355
Atmospheric-pressure MOVPE growth of InP using Lewis base monovalent cyclopentadienyl indium
K. Onuma, A. Kasahara, K. Kato, N. Aihara and T. Udagawa 360
Novel liquid precursors for the growth of InP and GaInAs epitaxial layers by MOVPE
F. Scholz, A. Molassioti, M. Moser, B. Notheisen, K. Streubel, M. Hostalek and L. Pohl 365
MOVPE growth of uniform AlGaAs and InGaAs using organoarsine with inverted-horizontal atmospheric-pressure reactor
T. Kikkawa, H. Tanaka and J. Komeno 370
MOVPE of AlN and GaN by using novel precursors
K.-L. Ho, K.F. Jensen, J.-W. Hwang, W.L. Gladfelter and J.F. Evans 376
Transition metal doping of LP-MOCVD-grown InP
T. Wolf, A. Krost, D. Bimberg, F. Reier, P. Harde, J. Winterfeld and H. Schumann 381
Purity of zinc precursors and the properties of epitaxial ZnSe grown by atmospheric pressure metalorganic chemical vapour deposition
H.M. Yates and J.O. Williams 386
MOVPE of ZnSe using organometallic allyl selenium precursors
S. Patnaik, K.F. Jensen and K.P. Giapis 390

SECTION VI. GROWTH OF III–V STRUCTURES

VI.A. *Lattice matched heterostructures*

Growth of GaInAs bulk mixed crystals as a substrate with a tailored lattice parameter *
H.-J. Sell 396
High quality $Al_xGa_{1-x-y}In_yP$ alloys grown by MOVPE on (311)B GaAs substrates
A. Valster, C.T.H.F. Liedenbaum, M.N. Finke, A.L.G. Severens, M.J.B. Boermans, D.E.W. Vandenhoudt and C.W.T. Bulle-Lieuwma 403
Hetero-epitaxy of $ZnSiAs_2$/GaAs grown by atmospheric pressure MOVPE
N. Achargui, A. Benachemhou, A. Fourcaran, G. Bougnot, P. Coulon, J.P. Laurenti and J. Camassel 410
OMVPE growth and characterization of Bi-containing III–V alloys
K.Y. Ma, Z.M. Fang, R.M. Cohen and G.B. Stringfellow 416
GaSb/InAs heterojunctions grown by MOVPE
S.K. Haywood, R.W. Martin, N.J. Mason, R.J. Nicholas and P.J. Walker 422
Investigation of MOCVD growth of $Al_xGa_{1-x}As$/GaAs and $Al_xGa_{1-x}As$/GaAs/$Al_xGa_{1-x}As$/GaAs multilayer structures with high Al content
Gao Hongkai, Yun Feng, Zhang Jikang, Hou Xun and Gong Ping 428
Optical and electrical properties of the $Al_xGa_{1-x}As$/GaAs single heterojunctions grown by low pressure MOVPE
F.E.G. Guimarães, I. Gyuro, F. Scheffer, M. Heuken and K. Heime 434
Low contact-resistance GaAs/AlGaAs regrowth interfaces and compositional grading layer formation during growth by metalorganic vapor phase epitaxy
K. Hiruma, T. Haga, T. Usagawa and A. Ihara 440
Growth of highly uniform, reproducible InGaAs films in a multiwafer rotating disk reactor by MOCVD
M.A. McKee, P.E. Norris, R.A. Stall, G.S. Tompa, C.S. Chern, D. Noh, S.S. Kang and T.J. Jasinski 445
Scanning transmission electron microscopy of heterointerfaces grown by metalorganic vapor phase epitaxy (MOVPE)
H. Lakner, B. Bollig, E. Kubalek, M. Heuken, K. Heime, F. Scheffer and F.E.G. Guimarães 452

VI.B. *Strained layers and alternative substrates*

MOVPE growth and characterization of strained layers *
M.-E. Pistol, A. Gustafsson, M. Gerling, L. Samuelson and H. Titze 458
Surface morphology improvement of GaAs-on-Si using a two-reactor MOCVD system and an AlAs/GaAs low temperature buffer layer: an approach to crack-free GaAs-on-Si
T. Nishimura, K. Kadoiwa, N. Hayafuji, M. Miyashita, K. Mitsui, H. Kumabe and T. Murotani 468

MOCVD growth of GaAs on Si using (Al,In)GaAs/GaAs buffer layer
K. Fujita, Y. Shiba and K. Asai 473
Very low dislocation density GaAs on Si using superlattices grown by MOCVD
T. Soga, H. Nishikawa, T. Jimbo and M. Umeno 479
Optical quality improvement of MOVPE grown GaAlAs/GaAs double heterostructures on silicon substrates
N. Draïdia, R. Azoulay, L. Dugrand, A.C. Papadopoulo, Y. Gao, B. Sermage, P. Ossart and J. Meddeb 483
High quality GaAs on Si using $Si_{0.04}Ge_{0.96}$/Ge buffer layers
R. Venkatasubramanian, M.L. Timmons, J.B. Posthill, B.M. Keyes and R.K. Ahrenkiel 489
LP-MOVPE growth of antiphase domain free InP on (001) Si using low temperature processing **
M. Grundmann, A. Krost and D. Bimberg 494
Critical layer thickness of MOVPE-grown GaAs on $In_xGa_{1-x}As$
J. te Nijenhuis, P.J. van der Wel, R.W.F. van Asten, P.R. Hageman and L.J. Giling 496
Improvement of the crystalline, optical and electrical quality of MOVPE GaInSb layers
G. Bougnot, F. Delannoy, F. Pascal, P. Grosse, A. Giani, J. Kaoukab, J. Bougnot, R. Fourcade, P.J. Walker, N.J. Mason and H. Lambert 502
MOVPE growth of GaN on a misoriented sapphire substrate
K. Hiramatsu, H. Amano, I. Akasaki, H. Kato, N. Koide and K. Manabe 509
MOVPE growth of GaP and $GaAs_xP_{1-x}$ on (111)-oriented GaP
H. Titze, M. Gerling, M.-E. Pistol and L. Samuelson 513
Absorption characteristics of GaSb/InAs and InSb/InAs SLSs grown on (111) GaAs by MOVPE **
M. Lakrimi, N.J. Mason, R.J. Nicholas, G.B. Stringfellow, G. Summers and P.J. Walker 518

VI.C. *Quantum wells*

Growth and analysis of quantum well structures *
D. Grützmacher 520
Temperature resolved photoluminescence investigations on InGaAs/InP MQWs
R. Schwedler, F. Reinhardt, D. Grützmacher and K. Wolter 531
Effect of growth parameters on the interfacial structure of GaInAs/InP quantum wells
J. Hergeth, D. Grützmacher, F. Reinhardt and P. Balk 537
Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence
J. Camassel, J.P. Laurenti, S. Juillaguet, F. Reinhardt, K. Wolter, H. Kurz and D. Grützmacher 543
Lateral and vertical composition control in MOCVD-grown InP/GaInAs(P) structures
C.G. Cureton, E.J. Thrush and A.T.R. Briggs 549
Determination of the band discontinuity of MOCVD grown $In_{1-x}Ga_xAs/In_{1-y}Al_yAs$ heterostructures with optical and structural methods
J. Böhrer, M. Grundmann, U. Lienert, D. Bimberg, H. Ishikawa, M. Kamada and N. Watanabe 555
MOVPE of In(GaAs)P/InGaAs MQW structures
P. Wiedemann, M. Klenk, W. Körber, U. Koerner, R. Weinmann, E. Zielinski and P. Speier 561
OMVPE growth of GaInAs/InP and GaInAs/GaInAsP quantum wells
H. Kamei and H. Hayashi 567
Influence of the gas switching sequence on the optical properties of ultrathin InGaAs/InP quantum wells
G. Landgren, P. Ojala and O. Ekström 573
MOVPE growth and optical properties of AlGaInP/GaInP strained single quantum well structures
M. Kondo, K. Domen, C. Anayama, T. Tanahashi and K. Nakajima 578
Investigation of $In_xGa_{1-x}As$/GaAs strained quantum well structures grown on non-planar substrates by MOCVD
P. Grodzinski, Y. Zou, J.S. Osinski and P.D. Dapkus 583
Patterning and overgrowth of nanostructure quantum well wire arrays by LP-MOVPE
N.H. Karam, A. Mastrovito, V. Haven, K. Ismail, S. Pennycook and H.I. Smith 591

SECTION VII. II–VI SEMICONDUCTORS

VII.A. *Narrow gap II–VI semiconductors*

MOVPE of narrow band gap II–VI materials *
R. Triboulet 598

The growth of CMT on GaAs for high quality linear arrays of MWIR and LWIR photodiodes
L.M. Smith, C.F. Byrne, D. Patel, P. Knowles, J. Thompson, G.T. Jenkin, T. Nguyen Duy, A. Durand and M. Bourdillot 605
Low temperature MOCVD of $Hg_{1-x}Cd_xTe$ on 311, 511, 711 and shaped GaAs
G.N. Pain, C. Sandford, G.K.G. Smith, A.W. Stevenson, D. Gao, L.S. Wielunski, S.P. Russo, G.K. Reeves and R. Elliman 610
Reaction measurements and growth of HgTe/CdTe by photo-assisted MOCVD using an excimer laser
Y. Fujita, T. Terada, S. Fujii and T. Iuchi 621
Low temperature growth of (Cd,Hg)Te layers by MOVPE
F. Desjonquères, A. Tromson-Carli, P. Cheuvart, R. Druilhe, C. Grattepain, A. Katty, Y. Marfaing, R. Triboulet and D. Lorans 626
HRTEM studies of defects and interdiffusion in $Hg_{1-x-y}Mn_yCd_xTe$ ($0 \le x,\ y \le 1$) grown by low temperature MOCVD
G.N. Pain, C.J. Rossouw, S.R. Glanvill, R.S. Rowe, R.S. Dickson, G.B. Deacon and B.O. West 632

VII.B. *Wide gap II–VI semiconductors*

MOVPE growth of wide bandgap II–VI materials *
H. Kukimoto 637
Surface photochemical reactions for alkyl group elimination from precursors in OMVPE
Sz. Fujita, S. Maruo, H. Ishio, P.A. Murawala and Sg. Fujita 644
The effects of photo-assisted MOCVD on the doping of Na acceptors into ZnS epitaxial layers
T. Ohno and T. Taguchi 649
Effects of Ar ion laser irradiation on MOVPE of ZnSe using DMZn and DMSe as reactants
A. Yoshikawa, T. Okamoto and T. Fujimoto 653
High quality over-epilayer growth of ZnSe on Li^+-implanted ZnSe epilayers by atmospheric pressure MOVPE
T. Yodo, K. Ueda, K. Morio, K. Yamashita and S. Tanaka 659
MOVPE growth and characterisation of CdTe on CdS single crystal substrates
M.Y. Simmons, P.D. Brown and K. Durose 664
Raman characterization of ZnSe/GaAs MOVPE heterostructures
O. Pagès, M. Renucci, O. Briot, N. Tempier and R.L. Aulombard 670
Properties of $Zn_{1-x}Cd_xS$ ternary and $Zn_{1-x}Cd_xS_{1-y}Se_y$ quaternary thin films on GaAs grown by OMVPE
Sz. Fujita, S. Hayashi, M. Funato, T. Yoshie and Sg. Fujita 674
Doping of nitrogen in ZnSe films: improved doping properties in ZnSe/ZnSSe periodic layered structures grown on GaAs by MOVPE
I. Suemune, H. Masato, K. Nakanishi, Y. Kuroda and M. Yamanishi 679

SECTION VIII. HIGH T_c SUPERCONDUCTORS AND OXIDES

MOCVD superconducting oxide films *
T. Hirai and H. Yamane 683
Fabrication and characterization of Bi–Sr–Ca–Cu–O MOCVD thin films
T. Sugimoto, M. Yoshida, K. Yamaguchi, Y. Yamada, K. Sugawara, Y. Shiohara and S. Tanaka 692
In-situ growth of YBCO high-T_c superconducting thin films by plasma-enhanced metalorganic chemical vapor deposition
J. Zhao, C.S. Chern, Y.Q. Li, D.W. Noh, P.E. Norris, P. Zawadzki, B. Kear and B. Gallois 699
Preparation of properties of superconducting Bi–Sr–Ca–Cu–O thin films on polycrystalline silver substrates by organometallic chemical vapor deposition
J.M. Zhang, B.W. Wessels, D.S. Richeson and T.J. Marks 705
Preparation and properties of Ba-deficient superconducting thin Y–Ba–Cu–O films **
J. Souc, D. Machajdik, V. Smatko, V. Strbik, K. Fröhlich, S. Hrib, S. Stefanik, P. Kordos and J. Ivan 710
Growth studies of ferroelectric oxide layers prepared by organometallic chemical vapor deposition
L.A. Wills, W.A. Feil, B.W. Wessels, L.M. Tonge and T.J. Marks 712

SECTION IX. DEVICES

IX.A. *Lasers*

Quantum wire lasers by OMCVD growth on nonplanar substrates *
R. Bhat, E. Kapon, S. Simhony, E. Colas, D.M. Hwang, N.G. Stoffel and M.A. Koza 716

MOVPE of AlGaInP/GaInP heterostructures for visible lasers *
P. Roentgen, W. Heuberger, G.L. Bona and P. Unger 724
Structures for improved 1.5 μm wavelength lasers grown by LP-OMVPE; InGaAs–InP strained-layer quantum wells a good candidate *
P.J.A. Thijs, E.A. Montie and T. van Dongen 731
Metalorganic chemical vapor deposition of InGaAs-GaAs-AlGaAs strained-layer quantum well lasers *
P.K. York, K.J. Beernink, J. Kim, J.J. Alwan, J.J. Coleman and C.M. Wayman 741
Reproducible growth of narrow linewidth multiple quantum well graded index separate confinement distributed feedback (MQW-GRIN-SCH-DFB) lasers by MOVPE
T. Tanbun-Ek, R.A. Logan, H. Temkin, N.A. Olsson, M.C. Wu, A.M. Sergent and K.W. Wecht 751
Room temperature low threshold CW operation of MOCVD-grown AlGaAs/GaAs SQW lasers on Si substrates with SiO_2 back-coating
T. Egawa, H. Tada, Y. Kobayashi, T. Soga, T. Jimbo and M. Umeno 757
Low threshold 1.5 μm SCH-MQW lasers by atmospheric pressure MOVPE and direct comparison of low versus atmospheric pressure MOVPE laser growth
A. Ougazzaden, J.-D. Ganière, Y. Gao, E.V.K. Rao, B. Sermage, C. Kazmierski and A. Mircea 761
A new selective MOVPE regrowth process utilizing in-situ vapor phase etching for optoelectronic integrated circuits
K. Shimoyama, Y. Inoue, M. Katoh, H. Gotoh, Y. Suzuki and H. Yajima 767
Orientation dependence of S, Zn, Si, Te, and Sn doping in OMCVD growth of InP and GaAs: application to DH lasers and lateral p–n junction arrays grown on non-planar substrates
R. Bhat, C. Caneau, C.E. Zah, M.A. Koza, W.A. Bonner, D.M. Hwang, S.A. Schwarz, S.G. Menocal and F.G. Favire 772
Interaction of the dopants Mg and Si in $Al_xGa_{1-x}As$/GaAs heterolayers (MOVPE): application to DQW laser structures
L. Korte, R. Treichler, M. Schreiber, Ch. Tanner, G. Kristen, C. Hanke and G. Weimann 779
Growth and assessment of InGaAs/InGaAlAs/InP multiple quantum well lasers
R.W. Glew, P.D. Greene, G.D. Henshall, C. Lowney, J.P. Stagg, J.E.A. Whiteaway, B. Garrett and A.G. Norman 784
$In_{0.47}Ga_{0.53}As$–InP heterostructures for vertical cavity surface emitting lasers at 1.65 μm wavelength
R.D. Dupuis, D.G. Deppe, C.J. Pinzone, N.D. Gerrard, S. Singh, G.J. Zydzik, J.P. van der Ziel and C.A. Green 790
Strained-layer InGaAs/InGaAsP MQW structures and their application to 1.67 μm lasers grown by metalorganic vapor phase epitaxy
M. Yamamoto, M. Oishi, H. Sudo, J. Nakano and N. Tsuzuki 796
Lasing characteristics of InGaAs/InGaAsP MQW structures grown by low-pressure MOVPE
M. Rosenzweig, W. Ebert, D. Franke, N. Grote, B. Sartorius and P. Wolfram 802

IX.B. *Optoelectronic devices and circuits*

InP based optoelectronics *
N. Pütz 806
Selective MOVPE growth of GaAs on Si and its applications to LEDs
A. Ackaert, P. Demeester, L. Buydens, G. Coudenys, P. Van Daele and M. Renaud 822
Improvement of InP crystal quality grown on GaAs substrates and device applications
Tatsuya Kimura, Tadashi Kimura, E. Ishimura, F. Uesugi, M. Tsugami, K. Mizuguchi and T. Murotani 827
GaAs/GaAlAs surface emitting IR LED with Bragg reflector grown by MOCVD
T. Kato, H. Susawa, M. Hirotani, T. Saka, Y. Ohashi, E. Shichi and S. Shibata 832
Improving the performance of $InAs_{1-x}Sb_x$/InSb infrared detectors grown by metalorganic chemical vapor deposition
R.M. Biefeld, J.R. Wendt and S.R. Kurtz 836
Two-step MOVPE growth for planar InP/InGaAs/InP pin–FET combinations with locally diffused buffer layer
G. Ebbinghaus, R. Strzoda, T. Scherg, H. Albrecht, R. Penz and C. Lauterbach 840
Growth and characterization of AlGaAs/GaAs quantum well structures for the fabrication of long wavelength infrared detectors
Z.F. Paska, J.Y. Andersson, L. Lundqvist and C.-O.A. Olsson 845
Application of AP MOVPE to a new butt-coupling scheme
B. Rose, D. Remiens, V. Hornung and D. Robein 850
High optical and electrical quality GaInAs/InP, GaAs/InP double heterostructures for optoelectronic integration
J.P. André, J.N. Patillon, P. Riglet, J.Y. Lesiourd, H. Le Coz and B.G. Martin 855
The use of InP-based semiconductor reflective stacks for enhanced device performance
J. Thompson, A.K. Wood, A.J. Moseley, M.Q. Kearley, P.J. Topham, N. Maung and N. Carr 860

LP-MOVPE growth and characterization of wide-gap InGaAsP/InP layers ($\lambda_g < 1.2$ μm) for optical waveguide applications
F.W. Reier, P. Harde and H. Kaiser 867
A novel technique for the preservation of gratings in InP and InGaAsP and for the simultaneous preservation of InP, InGaAs, and InGaAsP in OMCVD
R. Bhat, M.A. Koza, C.E. Zah, C. Caneau, C.C. Chang, S.A. Schwarz, A.S. Gozdz, P.S.D. Lin and A. Yi-Yan 871
A new approach for the integration of optoelectronic devices using laser selective area epitaxy
H. Liu, J.C. Roberts, J. Ramdani, S.M. Bedair, J. Farari, J.P. Vilcot and D. Decoster 878

IX.C. *Electronic devices*

High frequency AlGaAs/GaAs heterojunction bipolar transistors: the role of MOVPE *
G. Packeiser, H. Tews and P. Zwicknagl 883
Qualification of OMVPE AlGaAs/GaAs HBT structures using nondestructive photoreflectance spectroscopy
N. Bottka, D.K. Gaskill, P.D. Wright, R.W. Kaliski and D.A. Williams 893
MOVPE growth of highly zinc-doped bases for GaAs/AlGaAs heterojunction bipolar transistors
S. Tanaka, M. Ohkubo, M. Irikawa and T. Kikuta 898
LPMOCVD growth of C doped GaAs layers and AlGaAs/GaAs heterojunction bipolar transistors
Y. Ashizawa, T. Noda, K. Morizuka, M. Asaka and M. Obara 903
Growth and performance of AlGaAs/GaAs heterostructure bipolar transistors
N. Nordell, B. Willén, C.-O.A. Olsson, U. Westergren and G. Landgren 909
AlGaAs/GaAs p-MODFET materials grown using intrinsic carbon doping
J.S. Roberts, K.C. Singh, C.C. Button, J.P.R. David and J. Woodhead 915
MOVPE grown high performance 0.25 μm AlGaAs/ InGaAs/GaAs pseudomorphic MODFETs
A.G. Thompson, H.M. Levy, B.-Y. Mao, G. Martin and G.Y. Lee 921
Electrical and structural characterization of GaAs on InP grown by OMCVD; application to GaAs MESFETs
R. Azoulay, A. Clei, L. Dugrand, N. Draïdia, G. Leroux and S. Biblemont 926
MOVPE of AlInAs HEMT structures *
L. Aina, M. Mattingly, M. Serio and E. Martin 932
Pseudomorphic n-InGaP/ InGaAs/GaAs grown by MOVPE for HEMT LSIs
M. Takikawa, T. Ohori, M. Takechi, M. Suzuki and J. Komeno 942
Growth and characterization of double barrier resonant tunnelling diodes
H. Tews, R. Neumann and R.D. Schnell 947
InAs–GaSb hot electron transistors grown by metalorganic chemical vapor deposition
K. Taira, F. Nakamura, I. Hase, H. Kawai and Y. Mori 952
Ultralow doping profiles for applications in 3D integrated varactor tuned oscillators grown by MOVPE
I. Gyuro, F. Scheffer, M. Joseph, B. Roth, M. Heuken and K. Heime 956

WORKSHOP ON MOMBE, CBE, GSMBE, AND RELATED TECHNIQUES

Current status review and future prospects of CBE, MOMBE and GSMBE *
W.T. Tsang 960
Growth mechanism studies in CBE/MOMBE *
T. Martin, C.R. Whitehouse and P.A. Lane 969
Incorporation of group III and group V elements in chemical beam epitaxy of GaInAsP alloys *
J.L. Benchimol, G. Le Roux, H. Thibierge, C. Daguet, F. Alexandre and F. Brillouet 978
Carbon incorporation in GaAs and AlGaAs grown by MOMBE using trimethylgallium *
C.R. Abernathy 982
Selective growth of InP/GaInAs in LP-MOVPE and MOMBE/CBE *
O. Kayser 989
Some comparisons of chemical beam epitaxy with gas source molecular beam epitaxy *
G.J. Davies, P.J. Skevington, E.G. Scott, C.L. Franch and J.S. Foord 999
MOMBE (metalorganic molecular beam epitaxy) growth of InGaAlAsSb system on GaSb *
H. Asahi, T. Kaneko, T. Okuno and S. Gonda 1009
Si and Ge gas-source molecular beam epitaxy (GSMBE) *
M. Suemitsu, F. Hirose and N. Miyamoto 1015

New starting materials for MOMBE *
M. Weyers 1021
Gas-source MBE growth and n-type doping of AlGaAs using TEG, TEA, AsH_3 and Si_2H_6 *
T. Fuji, H. Ando, A. Sandhu, H. Ishikawa and Y. Sugiyama 1030
Surface chemistry of a new III–V MOCVD reactant: $PhAsH_2$ on GaAs(100) **
A. Schütze, J. Zacheja, M. Weyers and D. Kohl 1036
Mechanistic aspects relating to the growth of $Ga_xIn_{1-x}As$ by CBE **
C.L. French, A.T.S. Wee, J.S. Foord and G.J. Davies 1038
Studies of the surface reactivity of novel hydride adduct precursors for CBE growth of III–V compounds **
J.S. Foord, A.J. Murrell, D. O'Hare, N.K. Singh, A.T.S. Wee and T.J. Whitaker 1040
Hydrogen-plasma and photo-effects on MOMBE of GaAs **
I. Suemune, K. Hamaoka, A. Kishimoto, T. Koui, Y. Honda and M. Yamanishi 1041
Doping of GaAs and InP in MOMBE using DEZn, TESn and DETe **
J. Musolf, D. Marx, A. Kohl, M. Weyers and P. Balk 1043
Applications of spectroellipsometry to the growth of GaAs and AlGaAs by metalorganic molecular beam epitaxy **
W.E. Quinn, D.E. Aspnes and S. Gregory 1045
In situ control of the growing surface in high vacuum MOVPE of GaAs **
J. Jönsson, K. Deppert, S. Jeppesen, G. Paulsson, L. Samuelson and P. Schmidt 1047
Selective growth of p^+-GaAs by metalorganic molecular beam epitaxy **
N. Furuhata, H. Shimawaki and A. Okamoto 1049
Growth and diffusion study of carbon doped GaAs superlattice grown by chemical beam epitaxy **
T.H. Chiu, J.E. Cunningham, J.A. Ditzenberger and W.Y. Jan 1051
Correlation of carbon incorporation from TEG and effective V/III ratio on the surface in MOMBE grown GaAs **
M. Kamp, G. Mörsch, M. Weyers and H. Lüth 1053
CBE growth of GaInAs–InP wafers for surface emitting lasers **
T.K. Uchida, T. Uchida, K. Mise, N. Yokouchi, F. Koyama and F. Iga 1055
Growth of GaInAs by chemical beam epitaxy **
J.F. Carlin, A. Rudra, R. Houdré, A. Staehli and M. Ilegems 1057
Monolayer epitaxial growth of GaInAs ternary by MOMBE **
H. Kawanishi and H. Ikeda 1060
On the growth of GaInAs by MOMBE (CBE) **
H. Heinecke, B. Baur, F. Höger, A. Miklis and B. Jobst 1062
CBE growth of InGaAs for optoelectronic applications **
F. Genova, G. Morello, G. Autore and L. Gastaldi 1065
The search for all-hydride MOMBE: examination of trimethylamine alane, trimethylamine gallane, and arsine **
D.A. Bohling, G.T. Muhr, C.R. Abernathy, A.S. Jordan, S.J. Pearton and W.S. Hobson 1068
The substrate–epitaxial interface of GaAs and InP grown by GSMBE **
K. Tappura, A. Salokatve, K. Rakennus, H. Asonen and M. Pessa 1070
Effects of surface pre-treatment and hydrogen on ALE of ZnSe on GaAs in MOMBE **
Y. Kawakami, T. Toyoda, Y.-H. Wu, Sz. Fujita and Sg. Fujita 1072
InGaAs MOMBE – system drift and material quality **
E. Woelk, M.E. Sherwin and G.O. Munns 1074
MOMBE growth of high quality GaAs/GaInP heterostructures **
Ph. Maurel, Ph. Bove, J.C. Garcia, J.P. Hirtz and M. Razeghi 1076

Author index 1077
Subject index 1091